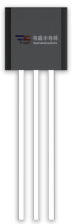
MPSL51 TRANSISTOR (PNP)



TO-92

1.EMITTER
2.COLLECTOR
3.BASE

FEATURES

- General Purpose Amplifier

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
MPSL51	TO-92	Bulk	1000pcs/Bag
MPSL51-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current	200	mA
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -0.1mA,I_E=0	-100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$*	I_C=-1mA,I_B=0	-100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.01mA,I_C=0	-4			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V,I_C=0			-0.1	μA
DC current gain	h_{FE}*	V_{CE}=-5V, I_C=-50mA	40		250	
Collector-emitter saturation voltage	$V_{CE(sat)(1)}$*	I_C=-10mA,I_B=-1mA			-0.25	V
	$V_{CE(sat)(2)}$*	I_C=-50mA,I_B=-5mA			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)(1)}$*	I_C=-10mA,I_B=-1mA			-1.2	V
	$V_{BE(sat)(2)}$*	I_C=-50mA,I_B=-5mA			-1.2	V
Transition frequency	f_T	V_{CE}=10V,I_C=10mA, f=20MHz	60			MHz
Collector output capacitance	C_{ob}	V_{CB}=10V,I_E=0, f=1MHz			8	pF

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.